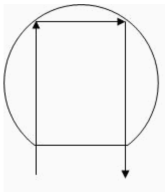
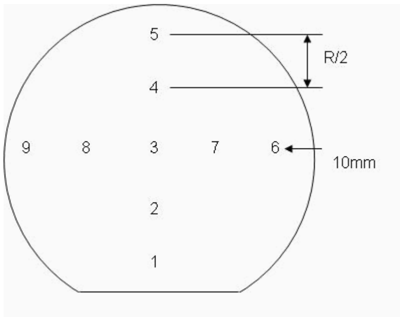
Category		**Parameter**	**Specification**	**Measurement Method**
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm	No Data
	2.0	Primary Flat Orientation	{110} +/- 0.5 degree	No Data
	3.0	Primary Flat Length	47.50 +/- 2.50 mm	No Data
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	612.00 +/- 16.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Flatness (SBIR)	<1.00um	20mm x 20mm, no partials, b/side ref, 100% UA
	8.0	Global Flatness (TIR)	<3.00um	ASTM F1530
	9.0	Bow	<60.00µm	ADE to ASTM F534
	10.0	Warp	<60.00µm	ADE to ASTM F657
	11.0	Edge Chips	0	Bright Light, 100% (note 2)
	12.0	Edge Exclusion	5mm	
	13.0	Bond Process	Reduced Bond Pin Pressure	Guaranteed by process
	14.0	Bond Anneal cycle	BOND ANNEAL CONDITIONS: 1150oC, 3hour. Dry.	Guaranteed by process
HandleSilicon	15.0	Handle Growth Method	CZ	Wafer Vendor
	16.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	17.0	Handle Thickness	600.00 +/- 15.00 µm	ADE, 100%
	18.0	Handle Doping Type	N	Wafer Vendor
	19.0	Handle Dopant	Phosphorous	Wafer Vendor
	20.0	Handle Resistivity	>1 Ohmcm	Wafer Vendor
	21.0	Backside Finish	Lapped and Etched with oxide and lasermark.	Guaranteed by process
	22.0	Backside Lasermark	Characters 12 to 17 [.5111A] SEMI M13, as per Xfab specification: 20M1.5111A and in consideration of PPCN_24052019	Guaranteed by process
BuriedOxide	23.0	Oxide Type	Thermal	
	24.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
	25.0	Oxide formed on	Handle Wafer	Guaranteed by process
DeviceSilicon	26.0	Front Surface	Mirror Polished	Guaranteed by process
	27.0	Device Growth Method	FZ	Wafer Vendor
	28.0	Oxygen Concentration	N.S	Wafer vendor
	29.0	Carbon Concentration	N.S	Wafer vendor
	30.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	31.0	Nominal Thickness	11.00 +/- 0.50 µm	Filmetrics, 100% 9-Pt (note3)
	32.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process

Part Number	Customer

Category		**Parameter**	**Specification**	**Measurement Method**
DeviceSilicon	33.0	Device Doping Type	P	Wafer Vendor
	34.0	Device Dopant	Boron	Wafer Vendor
	35.0	Device Resistivity	10 ~ 20 Ohm-cm	Wafer Vendor
	36.0	Voids	0	Bright Light, 100% (note 2)
	37.0	Scratches	none	Bright Light, 100% (note 2)
	38.0	Haze	none	Bright Light, 100% (note 2)
	39.0	LPD Count	<30 @ 0.3um	Tencor Particle Counter

Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below: 		
Additional Information			